NSN 5961-01-043-6253

Photo Semiconductor Device - Page 1 of 1

View Online at https://aerobasegroup.com/nsn/5961-01-043-6253

Inclosure Material:

Ceramic and metal and glass

Overall Length:

Between 0.102 inches and 0.115 inches

Overall Diameter:

Between 0.058 inches and 0.061 inches

Function For Which Designed:

Phototransistor

Internal Configuration:

Junction contact

Mounting Method:

Press fit

Features Provided:

Gold plated leads and hermetically sealed case

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

50.0 collector to emitter voltage, dc and 7.0 emitter to collector voltage, dc

Current Rating Per Characteristic:

0.50 milliamperes collector cutoff current, dc, emitter open and 3.00 milliamperes peak forward surge current

Power Rating Per Characteristic:

50.0 milliwatts small-signal input power, common-collector preset

Maximum Operating Tempurature Per Measurement Point:

125.0 degrees celsius ambient air

Special Features:

Junction pattern arrangement: npn

Precious Material And Location:

0case and terminal surfaces gold

Terminal Type And Quantity:

1 case and 2 tab, solder lug

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fiig:

A110a0